



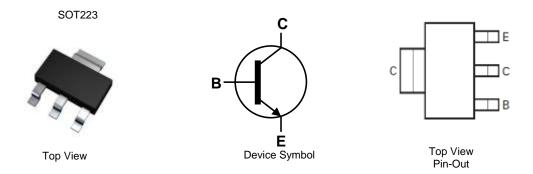
100V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 100V
- I_C = 6A High Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < 150mV @ 2A
- $R_{CE(SAT)} = 50m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 10A for a High Gain Hold-Up
- Complementary PNP Type: FZT953
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)



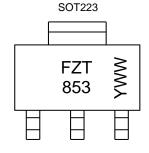
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT853TA	AEC-Q101	FZT853	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



FZT 853 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or $\overline{W}W$ = Week Code (01–53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	6	A
Peak Pulse Current	I _{CM}	10	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)		3.0 24	W mW/°C
Linear Derating Factor	(Note 6)	P _D	1.6 12.8	
Thermal Desistance Lunction to Ambient	(Note 5)	R _{θJA}	42	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	78	°C/W
Thermal Resistance Junction to Lead (Note 7)		R _{0JL}	8.8	
Operating and Storage Temperature Range	•	T _{J.} T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

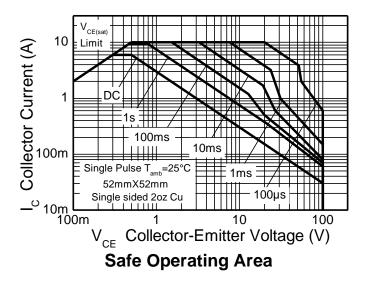
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

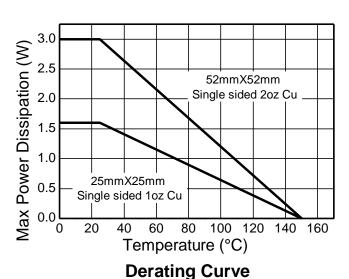
Notes:

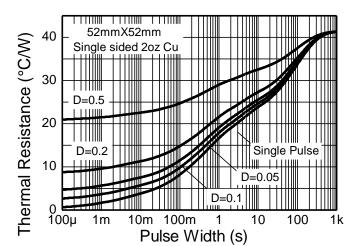
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information







Single Pulse T =25°C 52mmX52mm Single sided 2oz Cu Single sided 2oz Cu Single sided 2oz Cu Single Single Sided 2oz Cu Single Single Sided 2oz Cu Single Pulse Single Pulse T = 25°C 52mmX52mm Single Sided 2oz Cu Single Pulse T = 25°C 52mmX52mm Single Sided 2oz Cu Single Pulse T = 25°C 52mmX52mm Single Sided 2oz Cu Sided

Transient Thermal Impedance

Pulse Power Dissipation



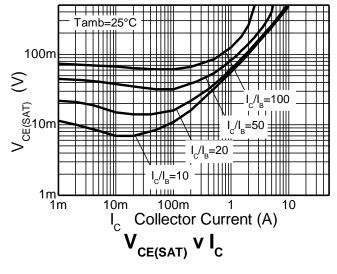
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

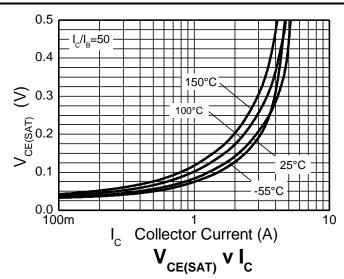
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	200	300	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	200	300	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	100	120	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	$I_E = 100\mu A$
Collector Cut-Off Current	I _{CBO}	_	<1	10	nA	V _{CB} = 150V
					μA	$V_{CB} = 150V, T_A = +100^{\circ}C$
Collector Cut-Off Current	I _{CER}	_	<1 —	10 1	nΑ μΑ	V_{CE} = 150V, $R_B \le 1kΩ$ V_{CE} = 150V, T_A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	<1	10	nA	V _{EB} = 6V
		100	200	_	_	I _C = 10mA, V _{CE} = 2V
DC Current Coin (Note 0)		100	200	300		$I_C = 2A$, $V_{CE} = 2V$
DC Current Gain (Note 9)	h _{FE}	50	100	_		I _C = 4A, V _{CE} = 2V
		20	30	_		I _C = 10A, V _{CE} = 2V
	V _{CE(SAT)}	_	14	50		$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	100	150	mV	$I_C = 2A$, $I_B = 100mA$
		_	250	340		$I_C = 5A$, $I_B = 500mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(SAT)}$	_	1,050	1,250	mV	$I_C = 5A$, $I_B = 500mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	900	1,100	mV	$I_{C} = 5A, V_{CE} = 2V$
Current Gain-Bandwidth Product (Note 9)	f _T	_	130	_	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz
Output Capacitance	Сово	_	35	_	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{ON}	_	50	_	no	$I_C = 1A, V_{CC} = 10V,$
Switching Times	t _{OFF}	_	1,650	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

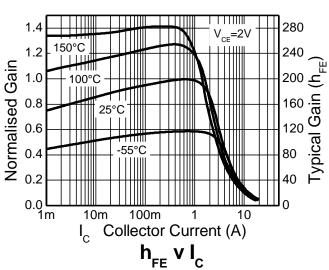
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

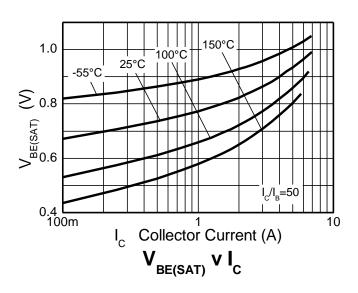


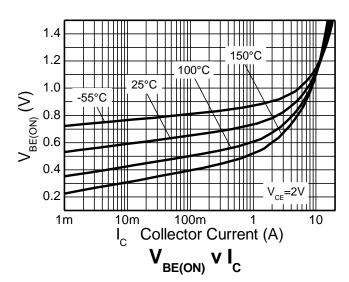
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







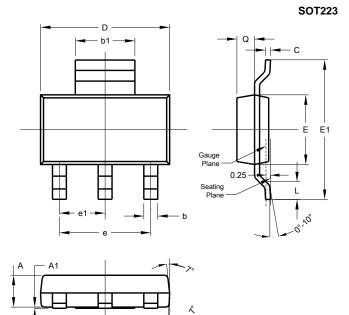






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

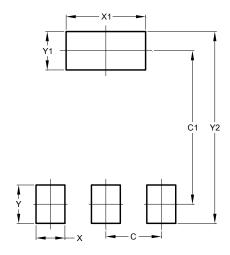


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
ø	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Χ	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

March 2017

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